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ATTY DOCKET NO.  
BUR920010184US.

SERIAL NO.  
10/695,336

Peter J. Geiss et al.

FILING  
10/28/03

GROUP  
2813

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
NB	6,294,442	9/2001	Kamal			
NB	5,683,935	11/1997	Miyamoto et al.			
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**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

		Becker et al., LOW RESISTANCE POLYCRYSTALLINE SILICON BY BORON OR ARSENIC IMPLANTATION AND THERMAL CRYSTALLIZATION OF AMORPHOUSLY DEPOSITED FILMS, J. Appl. Phys., Vol. 56, No. 4, 15 August 1984, pages 1233-1236
NB		Carbone et al., "Correlation of Ellipsometric Vol. Fraction to Polysilicon Grain Size from Transmission Electron Microscopy", Sept. 1999, IEEE/SEMI Adv. Semiconductor Mfg. Conf. and Workshop, pp. 359-367.

EXAMINER

Nema Berezny

DATE CONSIDERED

4-16-05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.